2SB649(A)

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

WR0459 I ṂṂ Ł SQS ÆṀ ɥ s ǁ ˥ Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

љ 5VG99<+D, Й ´

Complementary pair with 2SD669(A).

/ Applications

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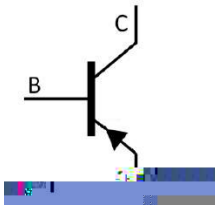
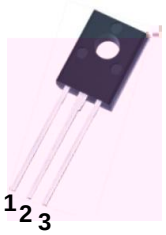
Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning

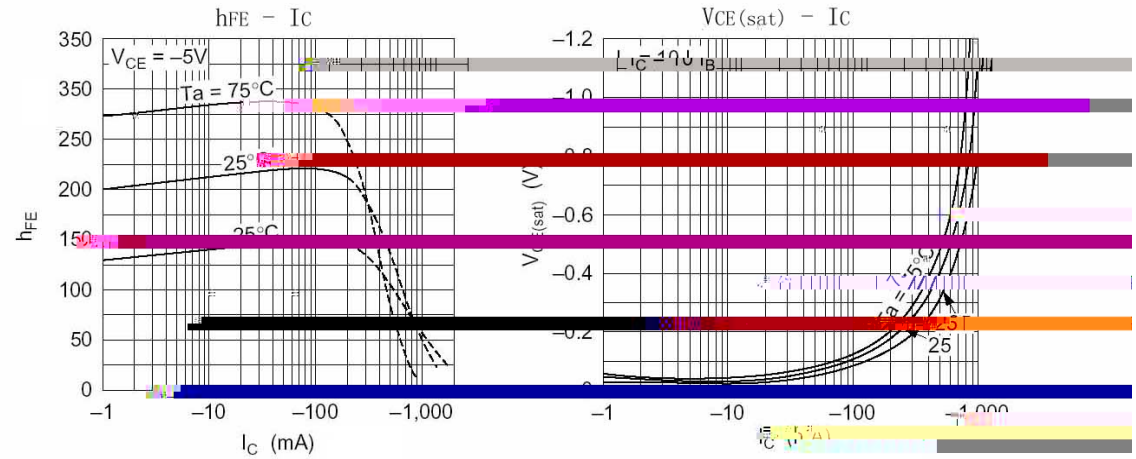


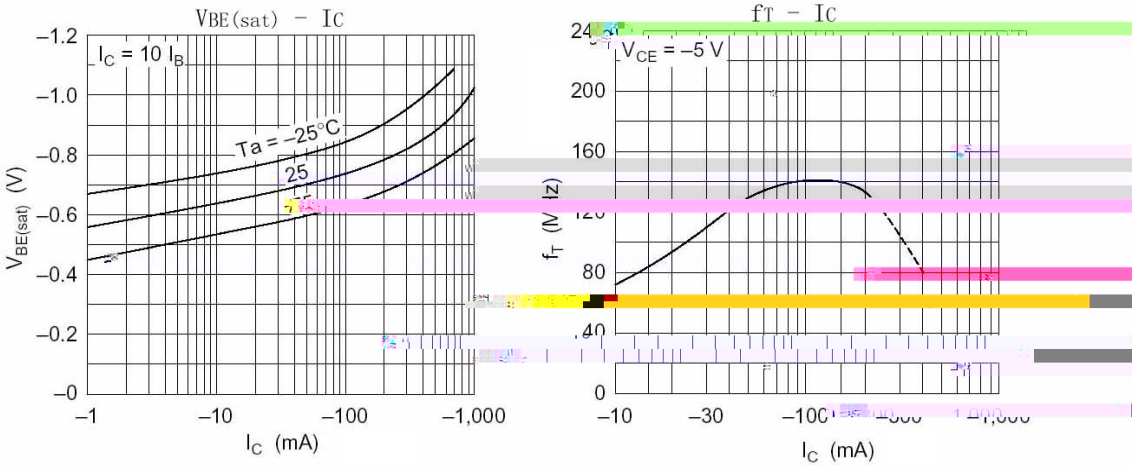
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

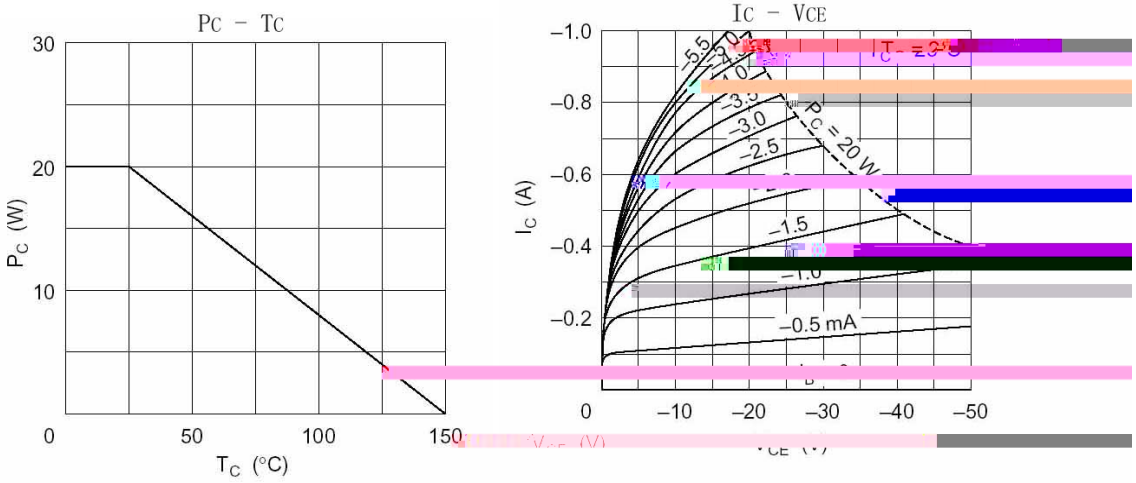
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

/ Electrical Characteristic Curve

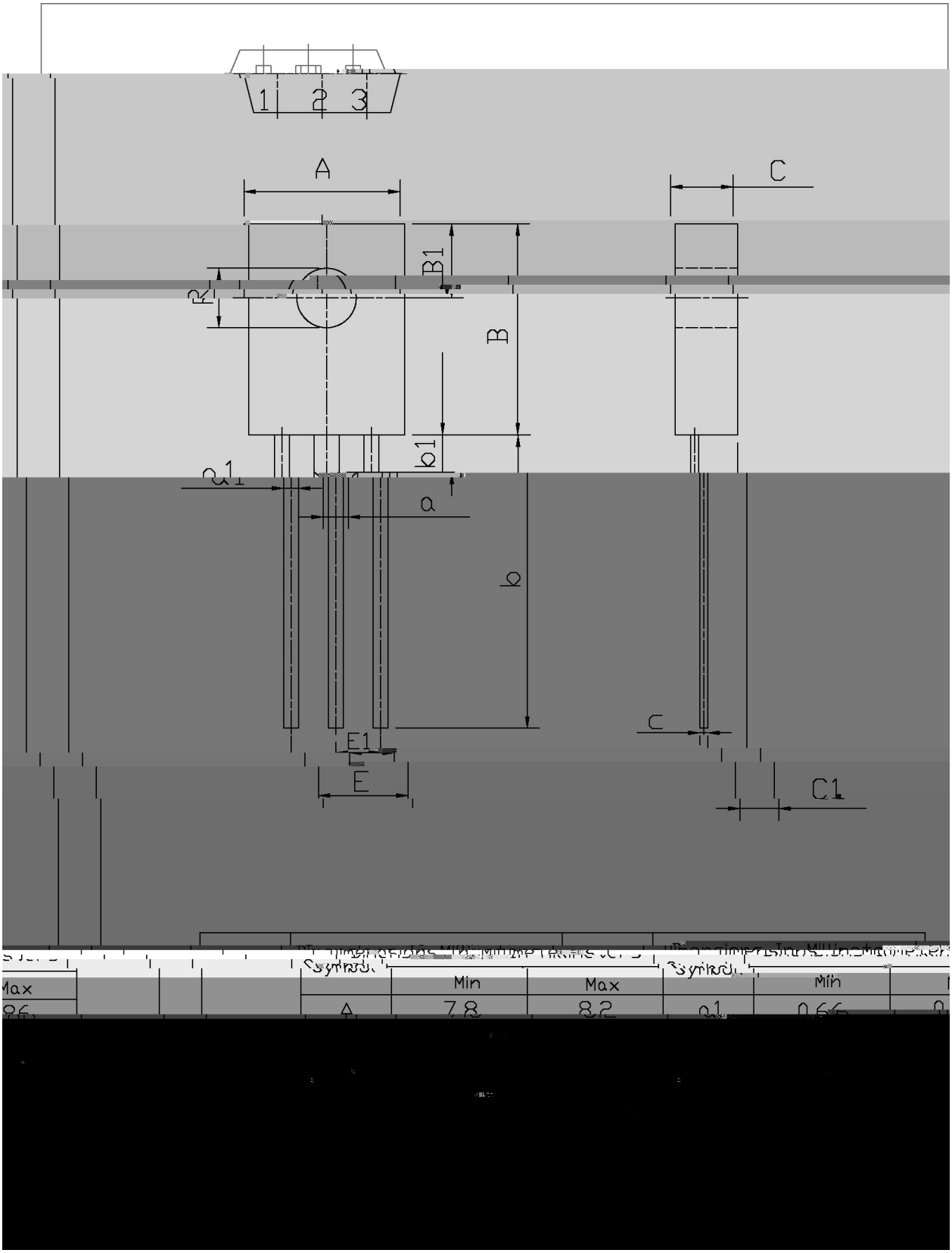






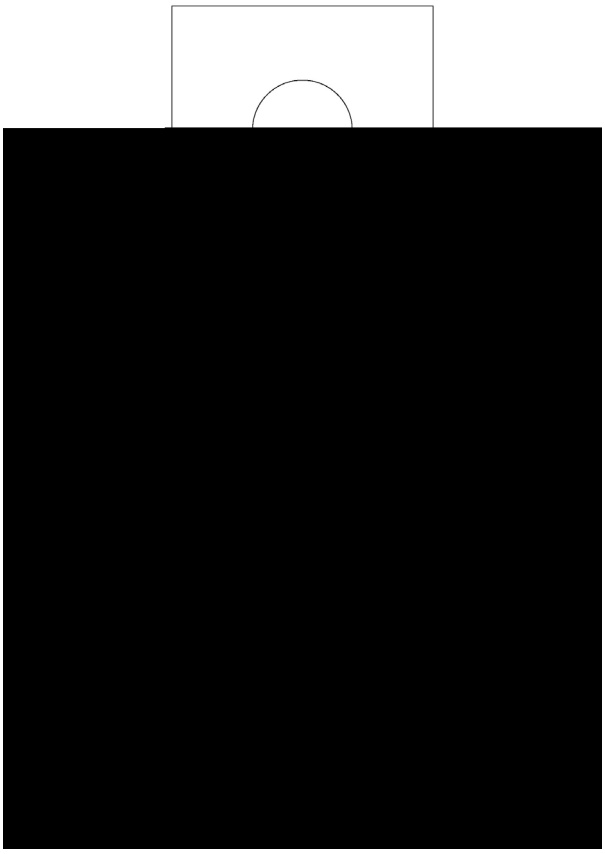
/ Package Dimensions

TO-126T 单位：mm



Max	Symbol	Min	Max	Symbol	Min	
86	A	7.8	8.2	c1	0.66	0

/ Marking Instructions



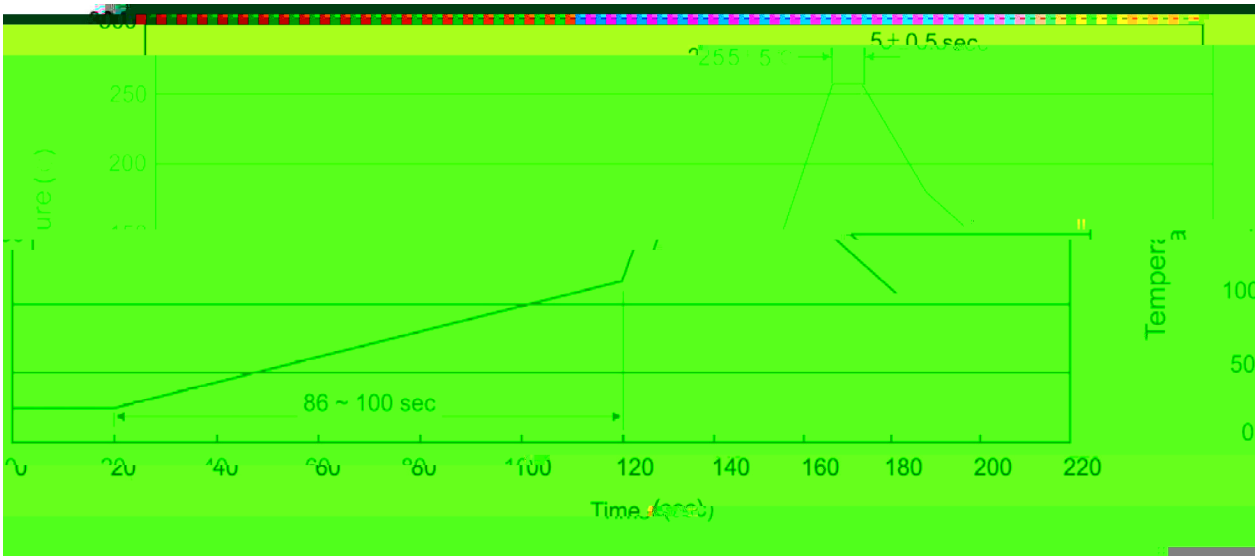
ب ˝ χ

EU χ	ⰼ ⰳ ⱈ ⱆ
E97< χ	ⰼ ⰴ ⱍ ⱆ
E=	ⰼ k_{IH} ˋ ⁶ ⱆ
---- χ	ⰼ ⰰ ⰲ ⱉ ⱍ ⱆ ⰰ ⱓ ⰰ ⰲ ⱉ ⱍ ⱐ ⱄ

Note:

BR:	Company Code
B649 :	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 ℓ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 255 ° 5 ɬ ı `H ڑ ˈY ⺈ ⺮ 5 ° 0.5sec;

3 ì ˙ ⺈ ˛ ɔ ھ ỷ ⺮ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

5	•	**Ủ 2**	**ỗ**	**ʙ**	**I**	255 °